

**PROCESS FOR PREPARING A STABILIZED
IDEAL OXYGEN PRECIPITATING SILICON WAFER**

ABSTRACT

The present invention is directed to a single crystal Czochralski-type silicon wafer, and a process for the preparation thereof, which has a non-uniform distribution of stabilized oxygen precipitate nucleation centers therein.

Specifically, the peak concentration is located in the wafer bulk and a
5 precipitate-free zone extends inward from a surface.